Docket No.: ASMEX.333A



INFORMATION DISCLOSURE STATEMENT

: Todd et al.

App. No.

10/074,564

Filed

: February 11, 2002

For

THIN FILMS AND METHODS OF

MAKING THEM

Examiner

Brook Kebede

Group Art Unit

2823

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing references that are also enclosed.

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 8 19 03

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	FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX.333A	APPLICATION NO. 10/074,564
6	1 P INTERMATION	DISCLOSURE STATEMENT		
	AUG 2 2 (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Todd et al.	
AUG			FILING DATE February 11, 2002	GROUP 2823

TO TRADEMINE							
			U.S. PATENT DOCUMENTS				
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
1.	5,214,002	05/25/93	Hayashi et al.				
2.	5,356,821	10/18/94	Naruse et al.				
3.	5,471,330	11/28/95	Sarma				
4.	6,103,600	08/15/00	Ueda et al.				

FOREIGN PATENT DOCUMENTS							
EXAMINER	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
INITIAL					_	YES	NO
5.	11317530	16-11-99	Japan (abstract)			Х	
6.	EP 0368651 A2	16-05-90					
7.	EP 0486047 A2	20-05-92					
8.	EP 0747974 A2	11-12-96					
9.	EP 1065728 A2	03-01-01					
10.	GB 2332564 A	23-06-99	United Kingdom			 -	
							†

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
11.	Olivares, J. et al.; "Solid-phase crystallization of amorphous SiGe films deposited by LPCVD on SiO ₂ and glass," Thin Solid Films 337 (1999) pp. 51-54.

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1	EXAMINER		11	DATE CONSIDERE	U	